

<b>SANYO</b>	No.1799D	<b>2SC3576</b>
		NPN Epitaxial Planar Silicon Transistor

**High  $h_{FE}$ , Low-Frequency  
General-Purpose Amp Applications**

**Applications**

- . LF general-purpose amplifiers, various drivers, muting circuit

**Features**

- . Adoption of FBET process
- . High DC current gain ( $h_{FE}=800$  to  $3200$ ).
- . Low collector-to-emitter saturation voltage ( $V_{CE(sat)} \leq 0.5V$ ).
- . High  $V_{EBO}$  ( $V_{EBO} \geq 15V$ ).

**Absolute Maximum Ratings at  $T_a=25^\circ C$**

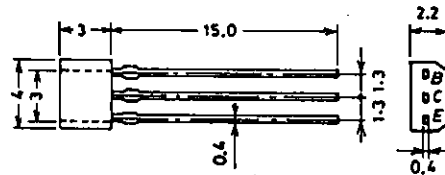
			unit
Collector to Base Voltage	$V_{CBO}$	30	V
Collector to Emitter Voltage	$V_{CEO}$	25	V
Emitter to Base Current	$V_{EBO}$	15	V
Collector Current	$I_C$	300	mA
Collector Current(Pulse)	$I_{CP}$	500	mA
Base Current	$I_B$	60	mA
Collector Dissipation	$P_C$	300	mW
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ C$

**Electrical Characteristics at  $T_a=25^\circ C$**

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=20V, I_E=0$			0.1	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=10V, I_C=0$			0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE}=5V, I_C=10mA$	800	1500	3200	
Gain-Bandwidth Product	$f_T$	$V_{CE}=10V, I_C=10mA$		250		MHz
Output Capacitance	$c_{ob}$	$V_{CB}=10V, f=1MHz$		2.7		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=200mA, I_B=4mA$		0.12	0.5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=200mA, I_B=4mA$		0.85	1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	30			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	15			V

**Package Dimensions 2033**

(unit: mm)



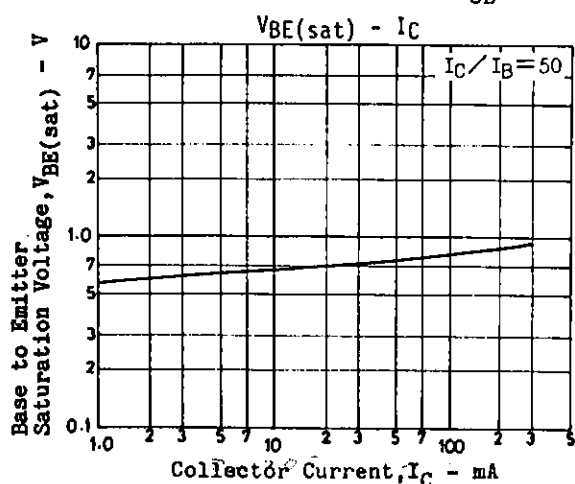
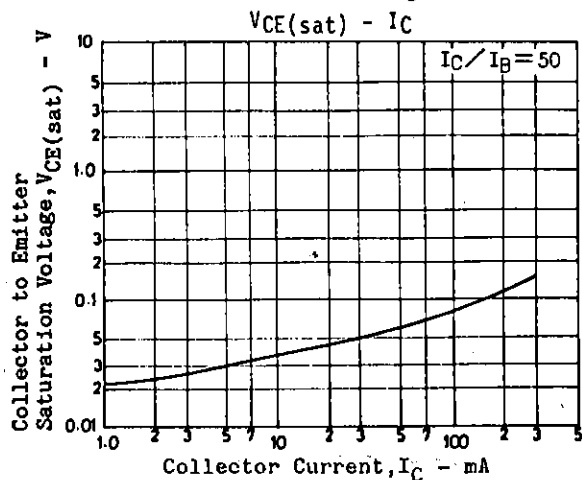
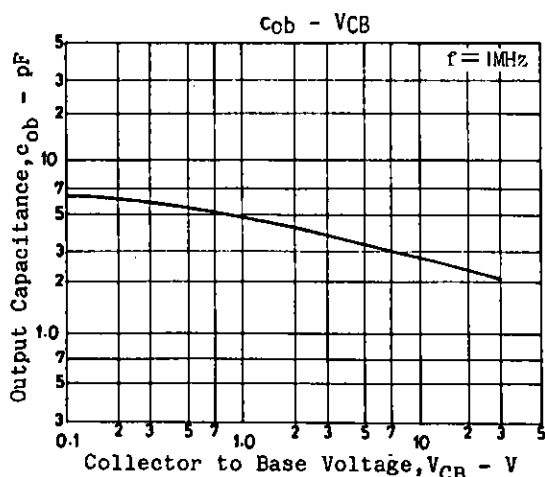
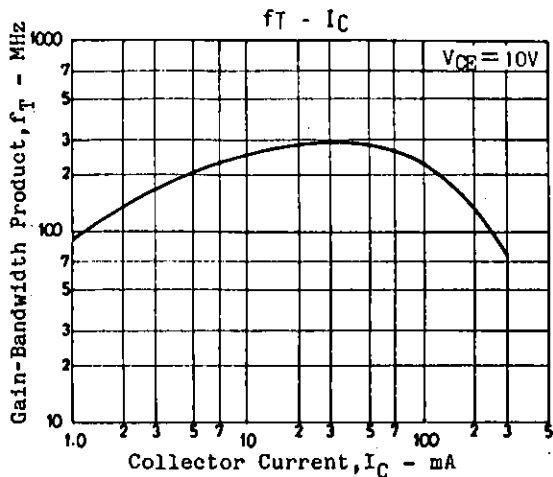
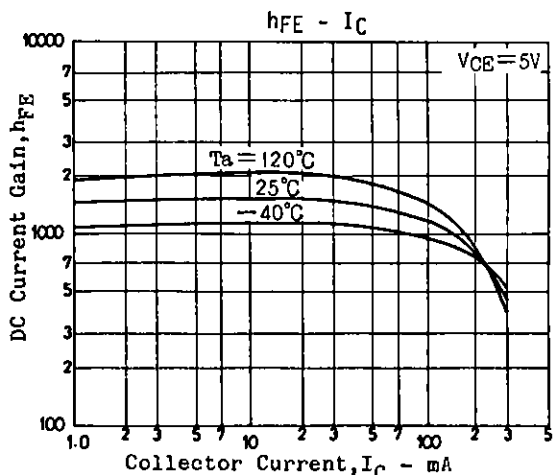
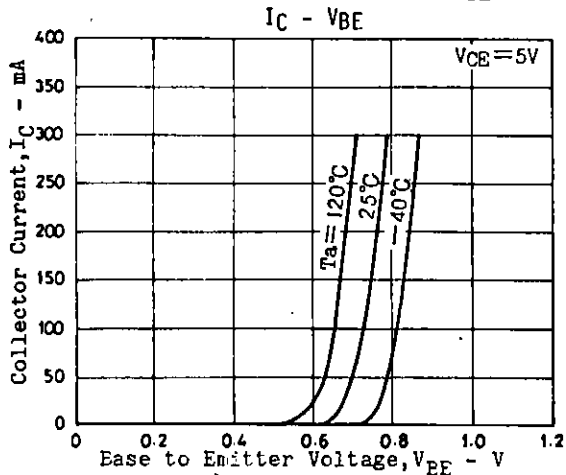
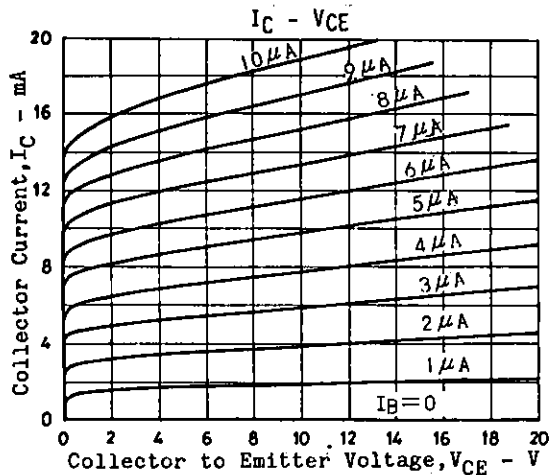
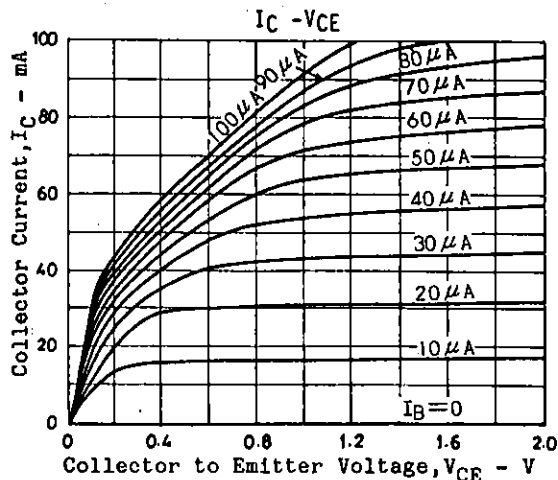
B: Base  
C: Collector  
E: Emitter

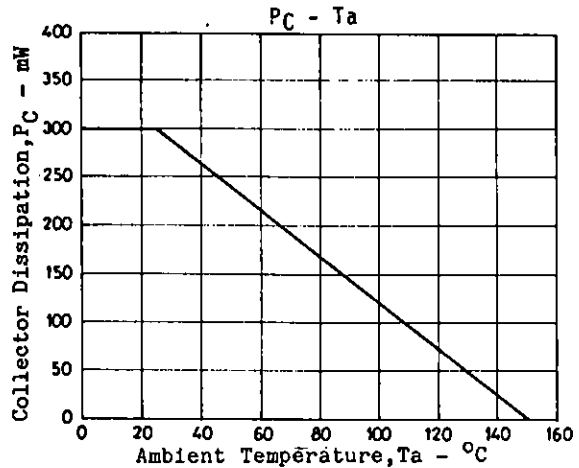
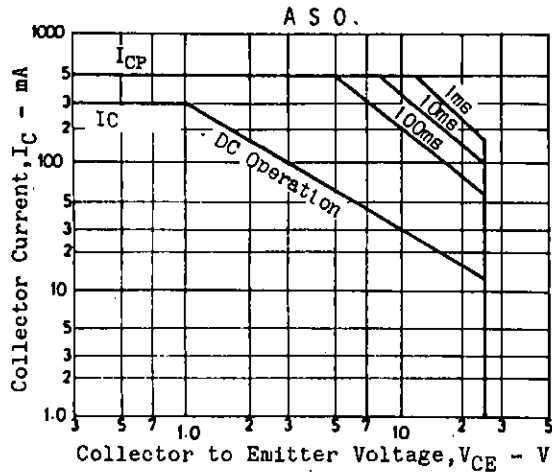
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